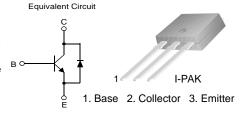


KSC5302DI

High Voltage & High Speed Power Switch Application

- Built-in Free-wheeling Diode makes efficient anti saturation operation Suitable for half-bridge light ballast Applications
- No need to interest an hFE value because of low variable storage-time spread even though corner spirit
- · Low base drive requirement



NPN Silicon Transistor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	800	V
V _{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	12	V
I _C	Collector Current (DC)	2	Α
I _{CP}	*Collector Current (Pulse)	5	Α
I _B	Base Current (DC)	1	Α
I _{BP}	*Base Current (Pulse)	2	Α
P _C	Power Dissipation(T _C =25°C)	25	W
T_J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 55 ~ 150	°C

Thermal Characteristics T_C=25°C unless otherwise noted

Symbol	Characteristics		Rating	Unit
$R_{\theta jc}$	Thermal Resistance	Junction to Case	5.0	°C/W
$R_{\theta ja}$		Junction to Ambient	83.3	

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Electrical Characteristics $\rm T_{C}{=}25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	$I_C=1$ mA, $I_E=0$	800	-	-	V
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_C=5$ mA, $I_B=0$	400	-	-	V
BV _{EBO}	Emitter Cut-off Current	I _E =1mA, I _C =0	12	-	-	V
I _{CBO}	Collector Cut-off Current	V _{CB} =500V, I _E =0	-	-	10	μΑ
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 9V, I_{C} = 0$	-	-	10	μΑ
h _{FE1} h _{FE2}	DC Current Gain	V _{CE} =1V, I _C =0.4A V _{CE} =1V,I _C =1A	20 10	-	-	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C =0.4A, I _B =0.04A I _C =1A, I _B =0.2A	-	-	0.4 0.5	V V
V _{BE} (sat)	Base-Emitter Saturation Voltage	I _C =0.4A, I _B =0.04A I _C =1A, I _B =0.2A	-	-	0.9 1.0	V V
C _{ob}	Output Capacitance	VCB = 10V, f=1MHz	-	-	75	pF
t _{ON}	Turn ON Time	V_{CC} =300V, I_{C} =1A	-	-	150	ns
t _{STG}	Storage Time	$I_{B1} = 0.2A, I_{B2} = -0.5A$ $R_L = 300\Omega$	-	-	2	μs
t _F	Fall Time		-	-	0.2	μs
t _{STG}	Storage Time	V _{CC} =15V,V _Z =300V	-	-	2.35	μs
t _F	Fall Time	$I_C = 0.8A, I_{B1} = 0.16A$ $I_{B2} = -0.16A$ $I_{C} = 200\mu H$	-	-	150	ns
V _F	Diode Forward Voltage	I _F = 0.4A I _F = 1A	-	-	1.2 1.5	V V
t _{rr}	* Reverse Recovery Time (di/dt = 10A/μs)	I _F = 0.2A I _F = 0.4A I _F = 1A	- - -	800 1.0 1.4	- - -	ns μs μs

*Pulse Test : Pulse Width=5, Duty cycles ≤ 10%

Typical Characteristics

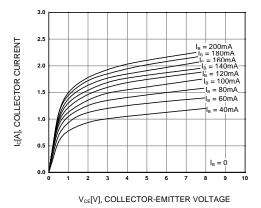


Figure 1. Static Characteristic

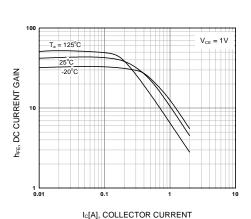


Figure 3. DC current Gain

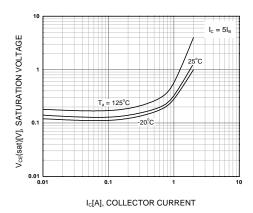


Figure 5. Collector-Emitter Saturation Voltage

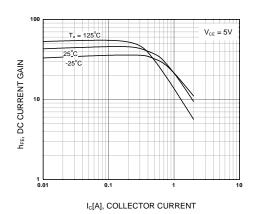


Figure 2. DC current Gain

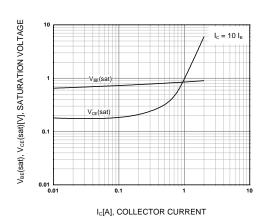


Figure 4. Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage

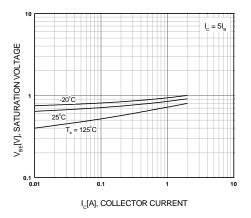


Figure 6. Base-Emitter Saturation Voltage

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Typical Characteristics (Continued)

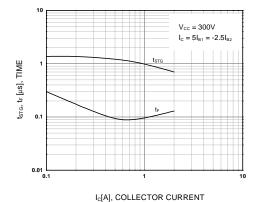


Figure 7. Switching Time

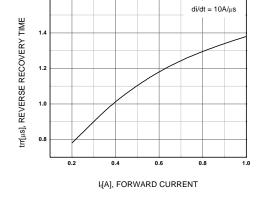


Figure 8. Forward Diode Voltage

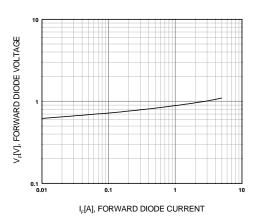


Figure 9. Reverse Recovery Time

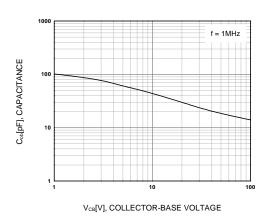


Figure 10. Collector Output Capacitance

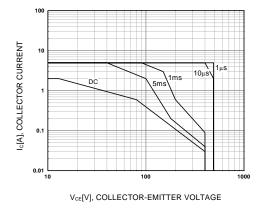


Figure 11. Safe Operating Area

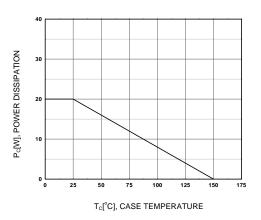
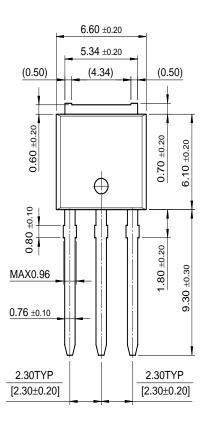


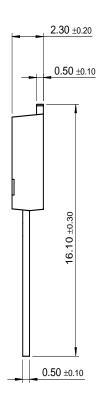
Figure 12. Power Derating

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Package Demensions

I-PAK







Dimensions in Millimeters

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